

Si Photo-diode Chip—TK0105PDN

1. Scope

- The specification applies to PIN silicon photo-diode chips.
- Type : TK0105PDN.

2. Structure

- PIN planar type.
- Electrode topside (anode) : Aluminum.
backside (cathode) : Au.

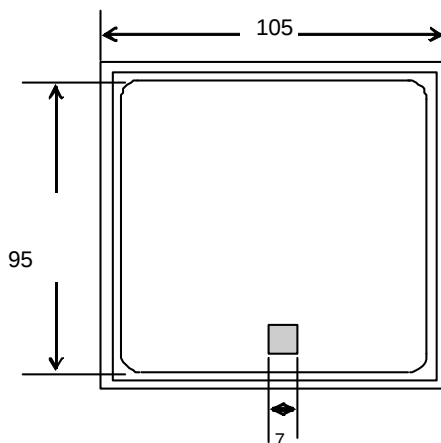
3. Size

- Chip size : 105mil × 105mil ± 2mil (2.667mm × 2.667mm ± 0.05mm)
- Thickness : 11.8mil ± 1mil (0.300mm ± 0.025mm)
- Active area : 95mil × 95mil (2.463mm × 2.463mm)
- Pattern drawing : per fig. 1

4. Electro-Optical Characteristics

(Ta = +25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit.
Forward Voltage	V _F	I _F =20mA		0.9	1.02	V
Reverse Breakdown Voltage	V _{BR}	I _R =30μA	100	150		V
Reverse Dark Current	I _D	V _R =10V			10	nA
Light Current	I _L	V _R =5V	13	25	37	μA
Peak Sensing Wavelength	λ _p			940		nm
Junction Capacitance	C _J	V _R =3V, F=1 MHz	5	10	15	pF



Unit : mil

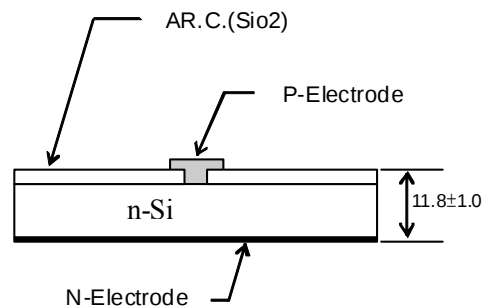


fig. 1

2014.Aug



☐ TYNTEK Head Office
☐ TYNTEK Chunan Branch
[http : //www.tyntek.com.tw](http://www.tyntek.com.tw)

Tel : 886-3-5781616

Tel : 886-37-582997

E-mail : service@serv.tyntek.com.tw

Fax : 886-3-5780545

Fax : 886-37-582908